

2SB0937 (2SB937), 2SB0937A (2SB937A)

Silicon PNP epitaxial planar type Darlington

For power amplification and switching
Complementary to 2SD1260, 2SD1260A

Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	2SB0937	V_{CBO}	-60	V
	2SB0937A		-80	
Collector-emitter voltage (Base open)	2SB0937	V_{CEO}	-60	V
	2SB0937A		-80	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_C	-2	A	
Peak collector current	I_{CP}	-4	A	
Collector power dissipation	$T_a = 25^\circ\text{C}$	P_C	35	W
			1.3	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

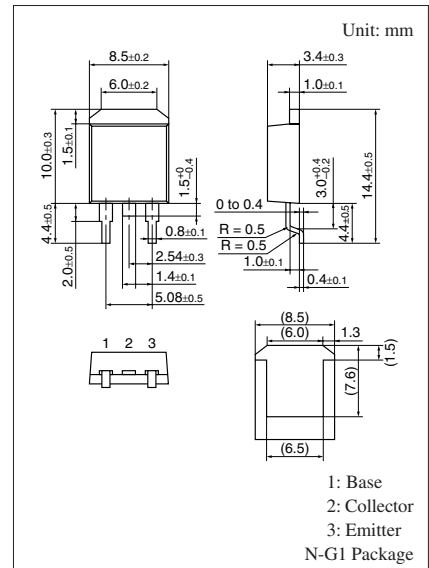
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0937	$I_C = -30\text{ mA}, I_B = 0$	-60			V
	2SB0937A		-80			
Base-emitter voltage	V_{BE}	$V_{CE} = -4\text{ V}, I_C = -2\text{ A}$			-2.8	V
Collector-base cutoff current (Emitter open)	2SB0937	$V_{CB} = -60\text{ V}, I_E = 0$			-1	mA
	2SB0937A		$V_{CB} = -80\text{ V}, I_E = 0$			
Collector-emitter cutoff current (Base open)	2SB0937	$V_{CE} = -30\text{ V}, I_B = 0$			-2	mA
	2SB0937A		$V_{CE} = -40\text{ V}, I_B = 0$			
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$	1000			—
	h_{FE2}^*	$V_{CE} = -4\text{ V}, I_C = -2\text{ A}$	2000		10000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{ A}, I_B = -8\text{ mA}$			-2.5	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -2\text{ A}$		0.4		μs
Storage time	t_{stg}	$I_{B1} = -8\text{ mA}, I_{B2} = 8\text{ mA}$		1.5		μs
Fall time	t_f	$V_{CC} = -50\text{ V}$		0.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

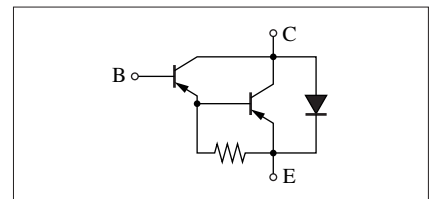
Rank	Q	P
h_{FE1}	2000 to 5000	4000 to 10000

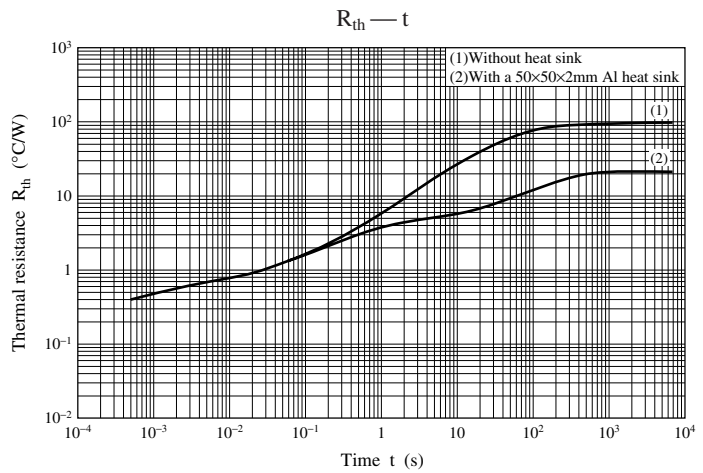
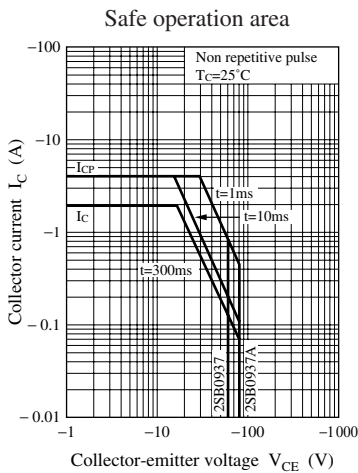
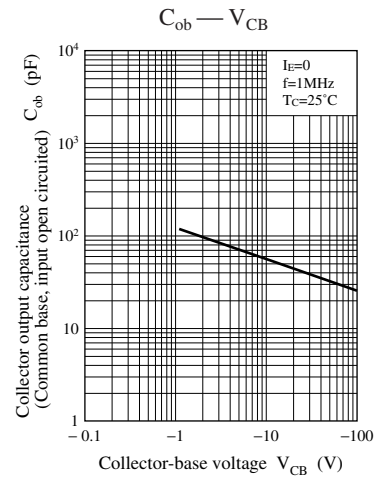
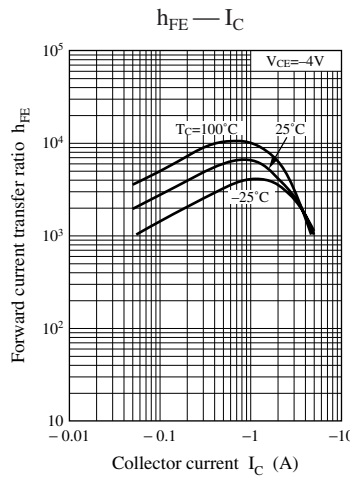
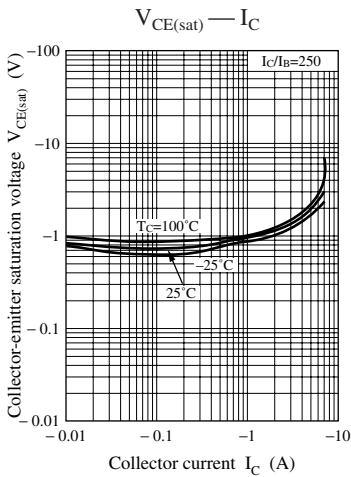
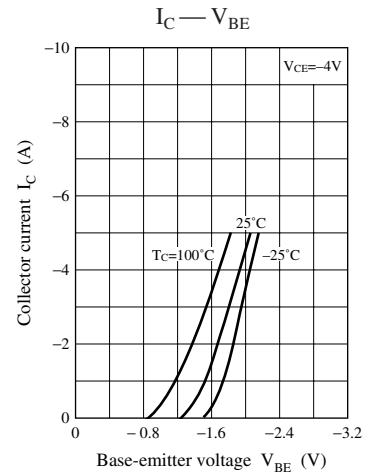
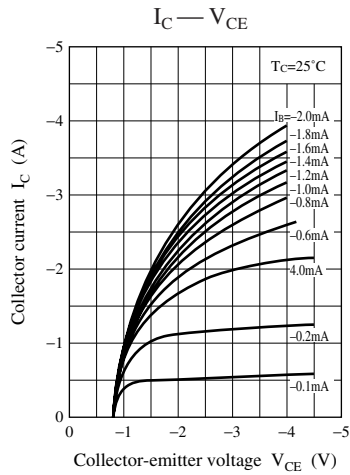
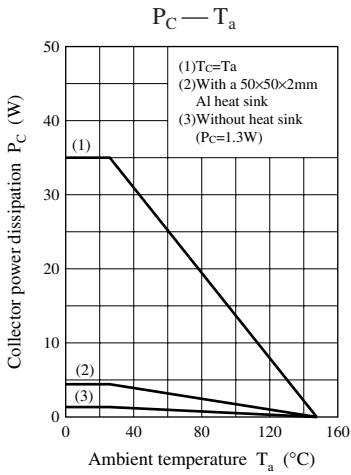
Note) The part number in the parenthesis shows conventional part number.



Note) Self-supported type package is also prepared.

Internal Connection





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